

Diamond, SiC and Nitride Wide Bandgap Semiconductors

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EDITORS:

Calvin H. Carter, Jr.

Cree Research Inc.
Durham, North Carolina, U.S.A.

Gennady Gildenblat

Pennsylvania State University
University Park, Pennsylvania, U.S.A.

Shuji Nakamura

Nichia Chemical Industries Ltd.
Tokushima, Japan

Robert J. Nemanich

North Carolina State University
Raleigh, North Carolina, U.S.A.



MATERIALS RESEARCH SOCIETY
Pittsburgh, Pennsylvania

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